N-Channel 30-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

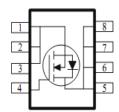
- DC/DC Conversion
- Power Routing
- Motor Drives

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)		
30	2.5 @ V _{GS} = 10V	100 ^c		
30	$4 @ V_{GS} = 4.5V$	100 ^c		









ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Limit	Units			
Drain-Source Voltage			30	V		
Gate-Source Voltage		V_{GS}	±20	V		
	T _A =25°C		37 ^a	A		
Continuous Drain Current	T _A =70°C	j I _D	29 ^a			
	T _C =25°C		100 ^c			
	T _C =70°C		100 ^c	A		
Pulsed Drain Current ^b	I_{DM}	120				
Continuous Source Current (Diode Conduction) a	I _S	6.6				
	T _A =25°C		5 ^a	W		
Power Dissipation	T _A =70°C	P _D	3.2 ^a			
Fower dissipation	T _C =25°C	l 'D	83			
	T _C =70°C		53			
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter			Maximum	Units			
Maximum Junction-to-Ambient ^a	t <= 10 sec	D	25	°C/W			
IMAXIIIUIII JUIICIIOII-IO-AIIIDIEIII	Steady State	$R_{\theta JA}$	65				
Maximum Junction-to-Case (Drain)	Steady State	$R_{\theta JC}$	1.5				

1

Notes

- a. Surface Mounted on 1" x 1" FR4 Board
- b. Pulse width limited by maximum junction temperature
- c. Package limited

Electrical Characteristics

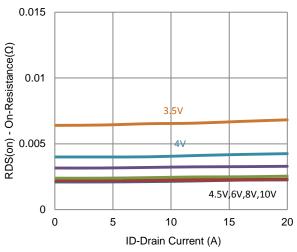
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$		1	uA		
Zero Gate Voltage Brain Gurrent	DSS	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$		10	u/\		
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	50			Α	
Drain-Source On-Resistance ^a	r	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$			2.5	mΩ	
	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$			4	11122	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		22		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 3.2 \text{ A}, V_{GS} = 0 \text{ V}$		0.76		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		78			
Gate-Source Charge	Q_gs	$I_{D} = 20 \text{ A}$		29		nC	
Gate-Drain Charge	Q_gd	10 - 23 //		27			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 15 \text{ V}, R_{L} = 3 \Omega,$		31			
Rise Time	t _r	$I_{DS} = 13 \text{ V}, \text{ NL} = 3.52,$ $I_{D} = 20 \text{ A},$		33		ne	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		177		ns	
Fall Time	t _f	VGEN = 10 V; NGEN 0 12		61			
Input Capacitance	C _{iss}			7955		_	
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		951		pF	
Reverse Transfer Capacitance	C_{rss}			693			

Notes

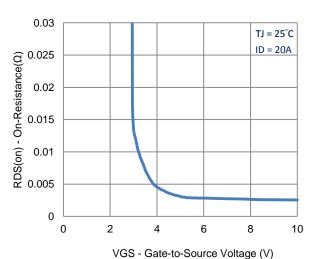
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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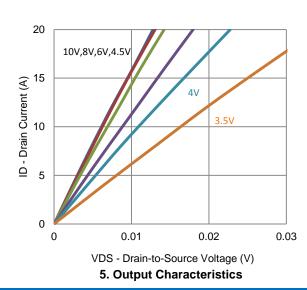
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current

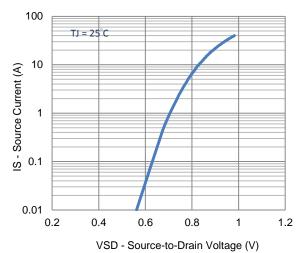


3. On-Resistance vs. Gate-to-Source Voltage

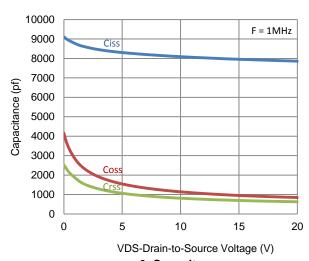


VGS - Gate-to-Source Voltage (V)

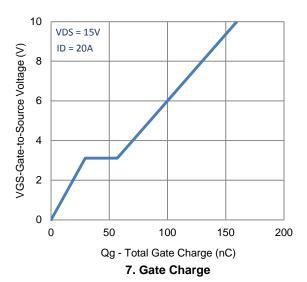
2. Transfer Characteristics

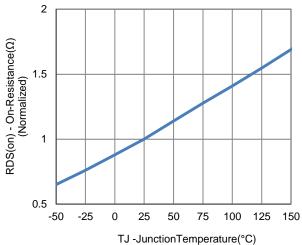


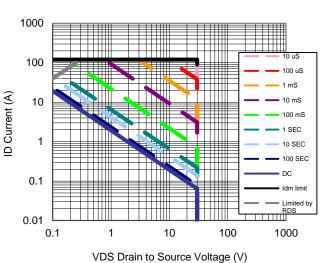
4. Drain-to-Source Forward Voltage



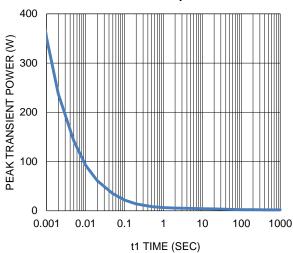
Typical Electrical Characteristics





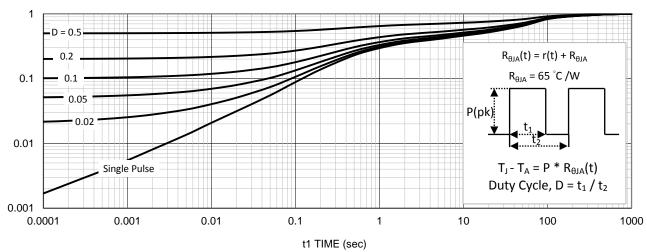






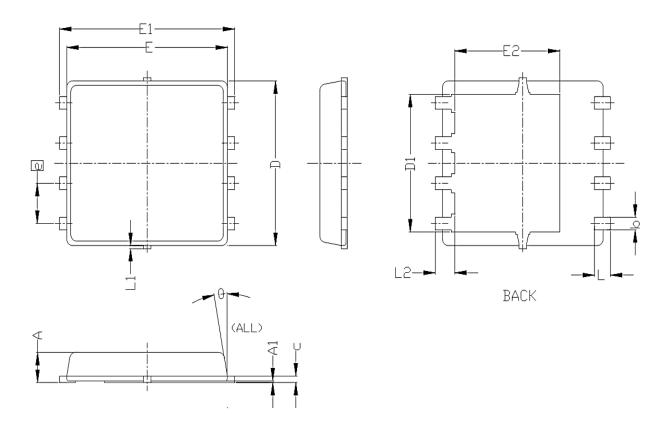
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS		DIMENSIONS IN INCHES				
STMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.85	0.95	1.00	0.033	0.037	0. 039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
С	0.15	0.20	0.25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1	4. 35 BSC			0. 171 BSC			
Е	5, 55 BSC 0, 219 BSC						
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC 0. 143 BSC						
e	1. 27 BSC			0.050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0. 027 REF			
θ	0°		10°	0°		10°	

5